

## 2SK2788

# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1033-0200

(Previous: ADE-208-538)

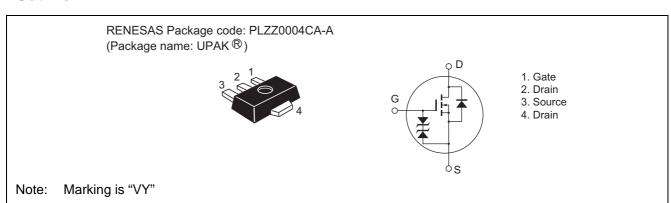
Rev.2.00

Sep.07,2005

#### **Features**

- Low on-resistance  $R_{DS(on)} = 0.12~\Omega~typ~(V_{GS} = 10~V,~I_D = 1~A) \label{eq:DS(on)}$
- Low drive current
- High speed switching
- 4 V gate drive devices.

#### **Outline**



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### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	2	А
Drain peak current	I <sub>D(pulse)</sub> *1	4	А
Body to drain diode reverse drain current	I <sub>DR</sub>	2	Α
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

2. When using the alumina ceramic board (12.5 x 20 x 0.7 mm)

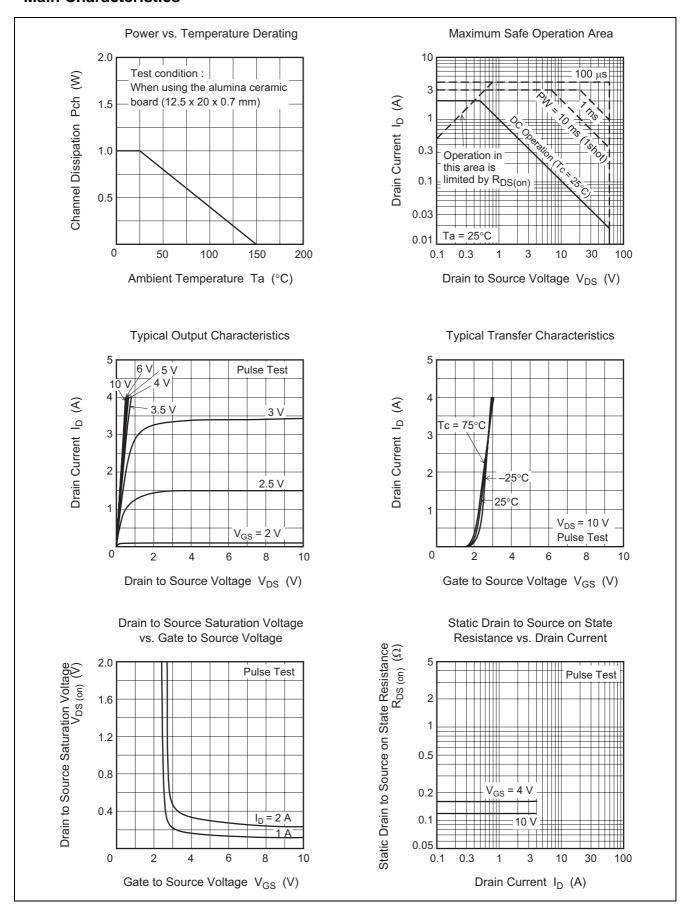
#### **Electrical Characteristics**

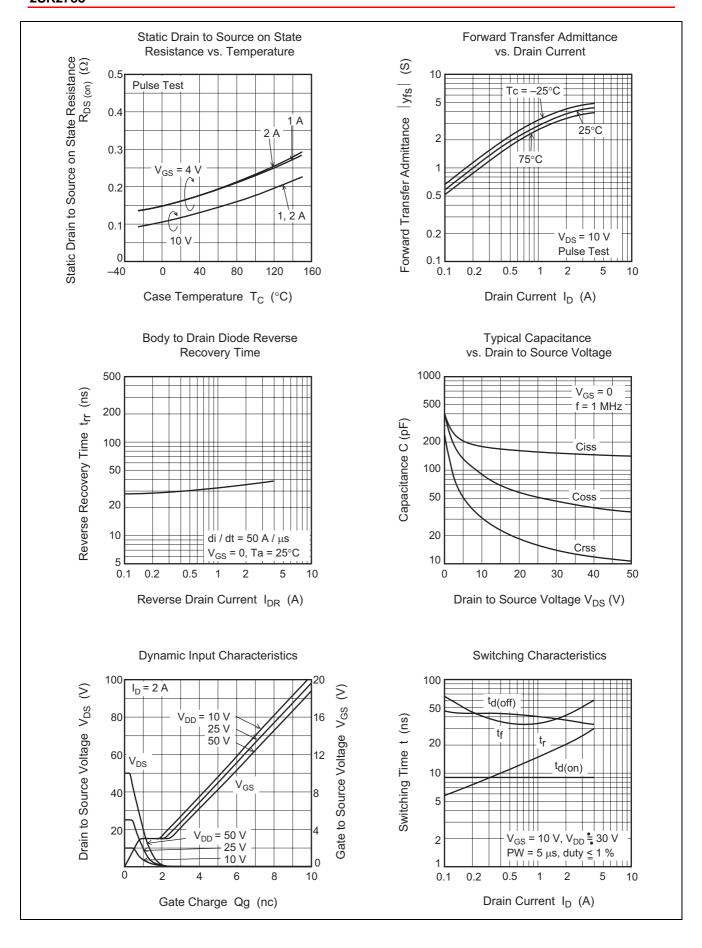
 $(Ta = 25^{\circ}C)$ 

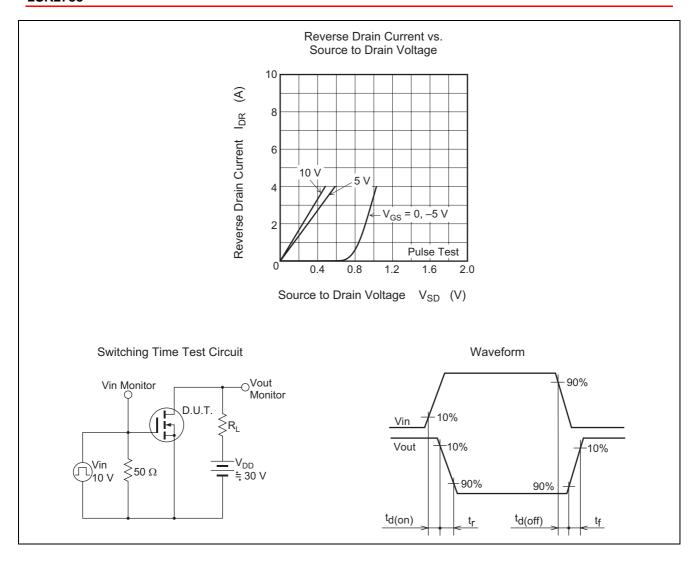
Item	Symbol	Min	Тур	Max	Unit	Test Conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$	
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state	R <sub>DS(on)</sub>	_	0.12	0.16	Ω	$I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$	
resistance	R <sub>DS(on)</sub>	_	0.16	0.25	Ω	$I_D = 1 \text{ A}, V_{GS} = 4 \text{ V}^{*3}$	
Forward transfer admittance	y <sub>fs</sub>	1.6	2.8	_	S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$	
Input capacitance	Ciss	_	180	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	_	90	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	_	30	_	рF		
Turn-on delay time	t <sub>d(on)</sub>	_	9	_	ns	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A},$	
Rise time	t <sub>r</sub>	_	15	_	ns	$R_L = 30 \Omega$	
Turn-off delay time	t <sub>d(off)</sub>	_	40	_	ns		
Fall time	t <sub>f</sub>	_	35	_	ns		
Body to drain diode forward voltage	$V_{DF}$	_	0.9	_	V	$I_D = 2 A, V_{GS} = 0$	
Body to drain diode reverse	t <sub>rr</sub>	_	35	_	ns	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0	
recovery time						$di_F/dt = 50A/\mu s$	

Notes: 3. Pulse test

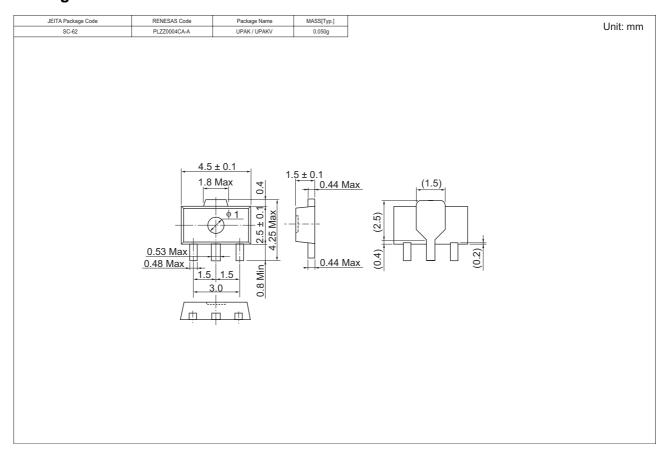
#### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container		
2SK2788VYTL-E	1000 pcs	Taping		
2SK2788VYTR-E	1000 pcs	Taping		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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